

PSMN017-60YS

N-channel LFPAK 60 V 15.7 m Ω standard level MOSFET

Rev. 02 — 1 April 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	-	60	V
I_D	drain current	$T_{mb} = 25 ^{\circ}\text{C}; V_{GS} = 10 \text{V};$ see Figure 1	-	-	44	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	74	W
Tj	junction temperature		-55	-	175	°C
Avalanc	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 45 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped	-	-	45	mJ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 30 \text{ A};$	-	4.4	-	nC
$Q_{G(tot)}$	total gate charge	V _{DS} = 30 V; see <u>Figure 14</u> and <u>15</u>	-	20	-	nC



Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{ or } 12}$	-	-	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 13}}{\text{ or } 100 \text{ c}}$	-	12.3	15.7	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	Q	
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 Ś
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN017-60YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$	-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	31	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	44	Α
I_{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	174	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	74	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-dr	ain diode				
Is	source current	T _{mb} = 25 °C	-	44	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$	-	174	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 45 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω; unclamped	-	45	mJ

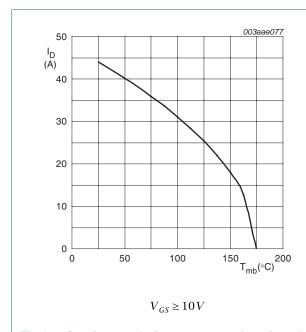


Fig 1. Continuous drain current as a function of mounting base temperature

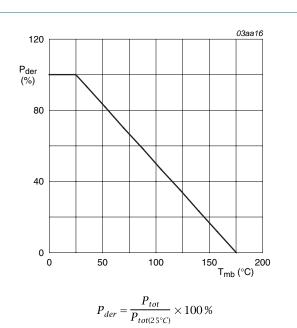


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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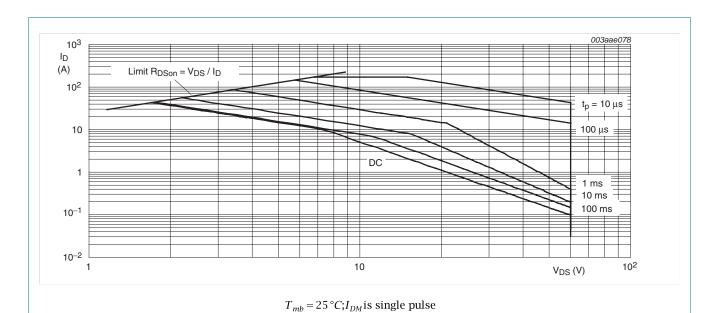


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.9	2.03	K/W

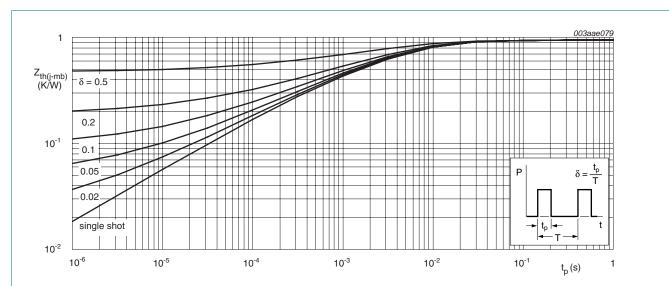


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6 Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 10</u> and <u>11</u>	2	3	4	V
V_{GSth}		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 11</u>	-	-	4.7	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.03	2	μΑ
		$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
I _{GSS} gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ	
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R _{DSon} drain-source on-s resistance	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 15 A; T_{j} = 175 °C; see <u>Figure 12</u>	-	24.7	36.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	-	25	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{ Figure } 13}$	-	12.3	15.7	mΩ
R_G	gate resistance	f = 1 MHz	-	1	1.5	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	20	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	16.5	-	nC
Q_{GS}	gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> and <u>15</u>	-	6.4	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u>	-	3.5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.9	-	nC
Q_{GD}	gate-drain charge	$I_D = 30 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 and 15	-	4.4	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 30 \text{ V}$; see Figure 14 and 15	-	4.8	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	1172	-	pF
C _{oss}	output capacitance	see Figure 16	-	164	-	pF
C _{rss}	reverse transfer capacitance		-	96	-	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1 \Omega; V_{GS} = 10 \text{ V};$	-	13	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	6.4	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	12.7	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dr	ain diode					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 17</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 10 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	33.4	-	ns
Q _r	recovered charge	$V_{DS} = 30 \text{ V}$	-	38.9	-	nC

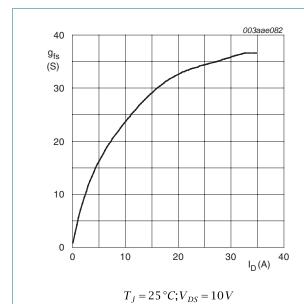


Fig 5. Forward transconductance as a function of drain current; typical values

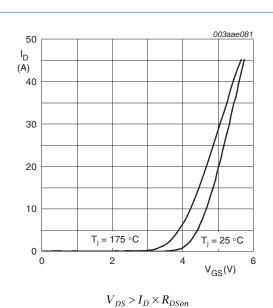


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

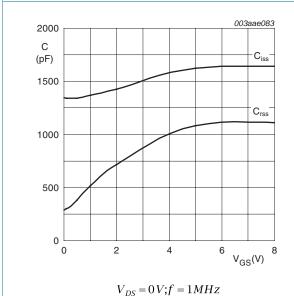
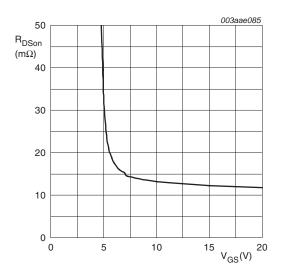


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; I_D = 10A$

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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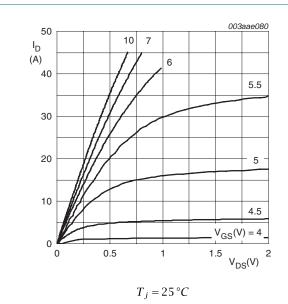


Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

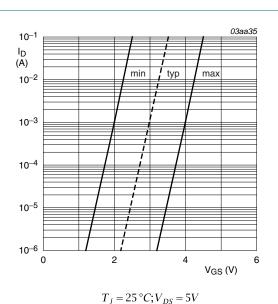


Fig 10. Sub-threshold drain current as a function of gate-source voltage

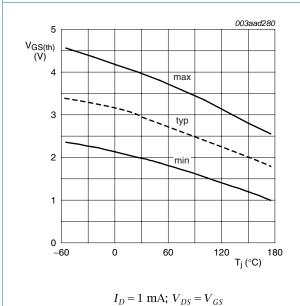
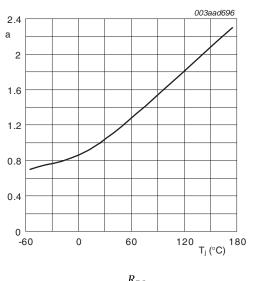


Fig 11. Gate-source threshold voltage as a function of

junction temperature



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

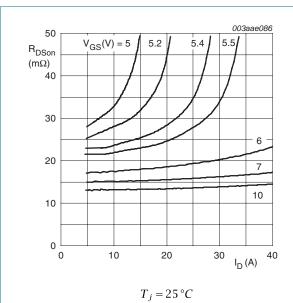


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

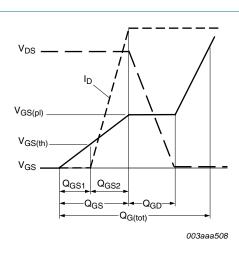


Fig 14. Gate charge waveform definitions

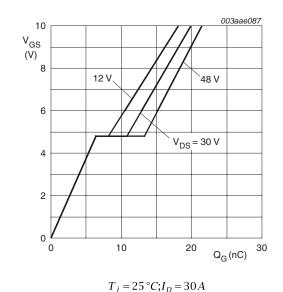
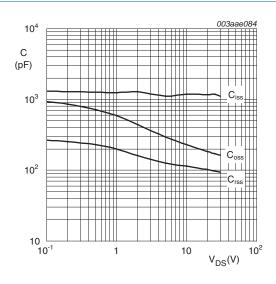
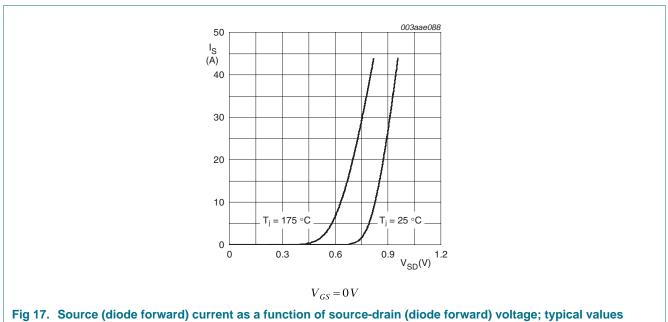


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669

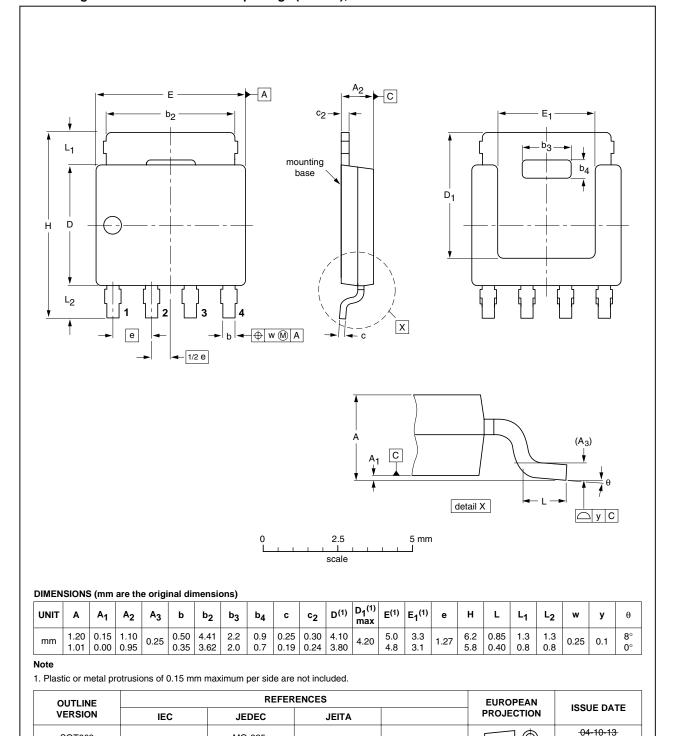


Fig 18. Package outline SOT669 (LFPAK)

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SOT669

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN017-60YS_2	20100401	Product data sheet	-	PSMN017-60YS_1
Modifications:		nged from objective to pa anges to content.	oduct.	
PSMN017-60YS_1	20100122	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel LFPAK 60 V 15.7 mΩ standard level MOSFET

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